

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		MMB DOCKET NO. 1890-0038	APPLICATION NO.: 10/757,360
		APPLICANT(S): Kriz et al.	
		FILING DATE: January 13, 2004	GROUP ART UNIT: 2812

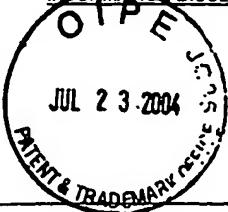
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
<i>CAF</i>	AA	6,319,786 B1	November 20, 2001	Gris			
	AB	5,185,276	February 9, 1993	Chen et al.			
	AC	5,204,276	April 20, 1993	Nakajima et al.			
	AD	5,587,326	December 24, 1996	Takemura			
	AE	5,001,533	March 19, 1991	Yamaguchi			
	AF	2001/0005035 A1	June 28, 2001	Kinoshita			
<i>CAF</i>	AG	2001/0003667 A1	June 14, 2001.	Ahn et al.			
	AH						
	AI						
	AJ						
	AK						

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
<i>CAF</i>	AL	DE 3940674 A1	June 28, 1990	Germany			Yes No
<i>CAF</i>	AM	DE 3304642 A1	August 16, 1984	Germany			Yes No
<i>CAF</i>	AN	FR 2795233 A1	June 18, 1999	France			Yes No
<i>CAF</i>	AO	CA 01 201 218	February 25, 1986	Canada			Yes No
	AP						Yes No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

<i>CAF</i>	AQ	1	Pontcharra, de Jean, et al., "A 30-GHz f_T Quasi-Self-Aligned Single-Poly Bipolar Technology", IEEE Transactions on Electron Devices, New York US, November 1, 1997, Volume 44, No. 11, pages 2091 – 2906, (6 pages).
<i>CAF</i>	AR	1	Sugiyama, M. et al., "A 40 GH f_T Si Bipolar Transistor LSI Technology", Proceedings of the International Electron Devices Meeting, Washington, Dec. 3-6, 1989, New York US, December 3, 1989, Pages 221 – 224, (4 pages)
<i>CAF</i>	AS	1	Aoyama T. et al., "Selective Polysilicon Deposition (SPD) by Hot-Wall LPCVD and its Application to High Speed Bipolar Devices", Japanese Journal of Applied Physics, Tokyo, Japan 1990, pages 665 – 668, (4 pages).

EXAMINER	<i>CAF</i>	DATE CONSIDERED <i>8/3/05</i>
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicants.		

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
BA						
BB						
BC						
BD						
BE						
BF						
BG						
BH						
BI						
BJ						
BK						

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION
BL						Yes No
BM						Yes No
BN						Yes No
BO						Yes No
BP						Yes No

OTHER (Including Author, Title, Date, Pertinent Pages, etc.)

<i>CB</i>	AQ	2	Burghartz J. N. et al., "Novel In-Situ Doped Polysilicon Emitter Process with Buried Diffusion Source (BDS)", IEEE Electron Device Letters, Volume 12, No. 12, New York US, December 1991, pages 679 - 681, (3 pages).
<i>CR</i>	AR	2	Selvakumar, C. R., "Theoretical and Experimental Aspects of Polysilicon Emitter Bipolar Transistors", IEEE, November 16, 1988, pages 3 - 16, (14 pages).
	AS	2	

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